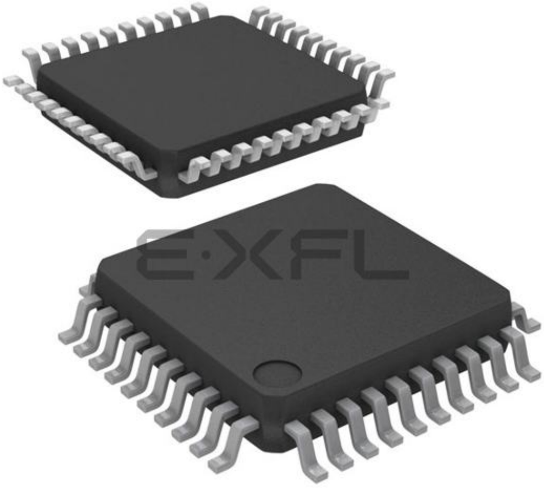
Renesas Electronics America Inc - R5F212L4SYFP#X6 Datasheet



What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	R8C
Core Size	16-Bit
Speed	20MHz
Connectivity	LINbus, SIO, UART/USART
Peripherals	POR, PWM, Voltage Detect, WDT
Number of I/O	25
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	1.5K x 8
Voltage - Supply (Vcc/Vdd)	2.2V ~ 5.5V
Data Converters	A/D 9x10b
Oscillator Type	Internal
Operating Temperature	-20°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	32-LQFP
Supplier Device Package	32-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f212l4syfp-x6

1.2 Product List

Table 1.5 lists the Product List for R8C/2K Group, Figure 1.1 shows a Part Number, Memory Size, and Package of R8C/2K Group, Table 1.6 lists the Product List for R8C/2L Group, and Figure 1.2 shows a Part Number, Memory Size, and Package of R8C/2L Group.

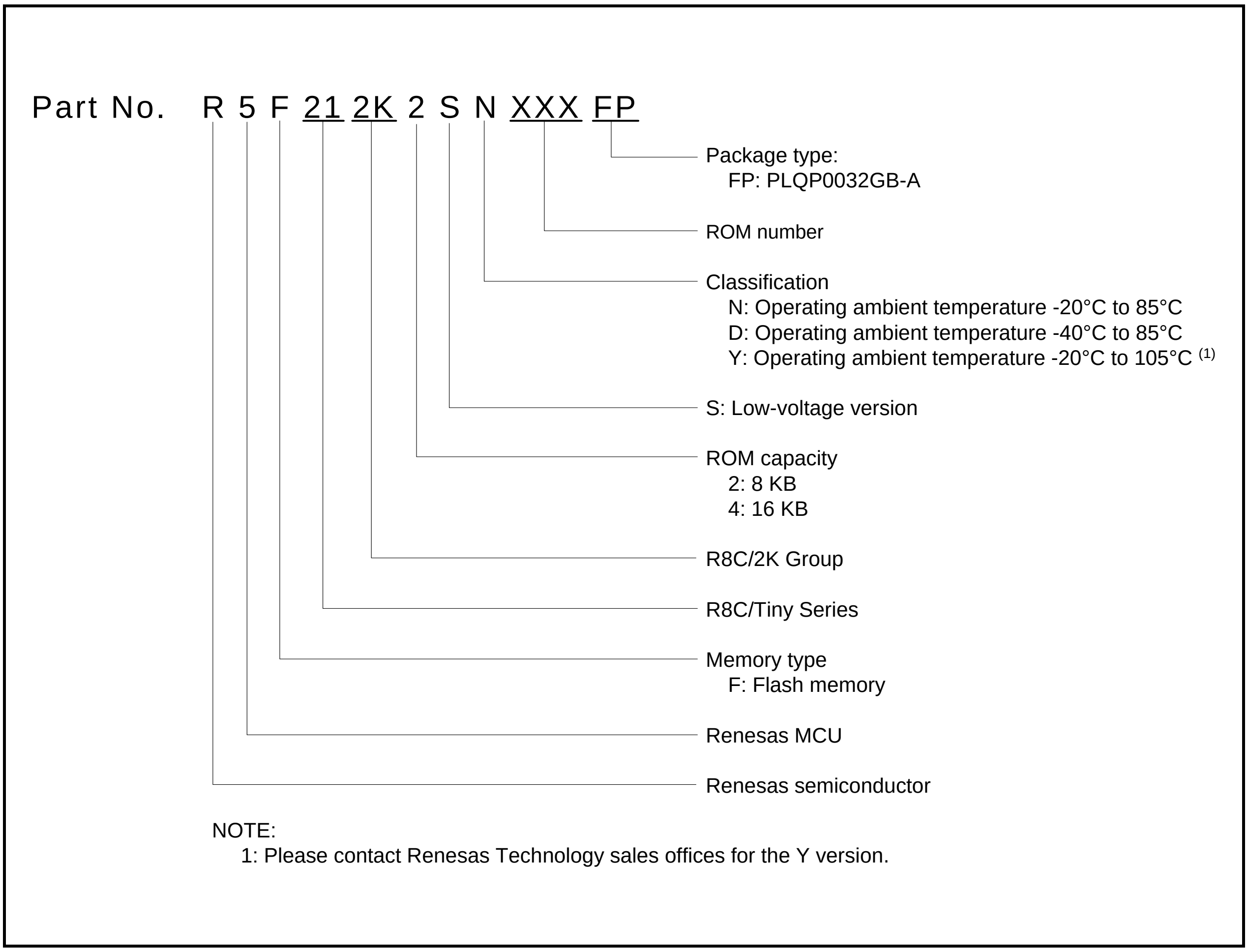
Table 1.5 Product List for R8C/2K Group **Current of Dec. 2007**

Part No.	ROM Capacity	RAM Capacity	Package Type	Remarks
R5F212K2SNFP	8 Kbytes	1 Kbyte	PLQP0032GB-A	N version
R5F212K4SNFP	16 Kbytes	1.5 Kbytes	PLQP0032GB-A	
R5F212K2SDFP	8 Kbytes	1 Kbyte	PLQP0032GB-A	D version
R5F212K4SDFP	16 Kbytes	1.5 Kbytes	PLQP0032GB-A	
R5F212K2SNXXXFP (D)	8 Kbytes	1 Kbyte	PLQP0032GB-A	N version Factory programming product(1)
R5F212K4SNXXXFP (D)	16 Kbytes	1.5 Kbytes	PLQP0032GB-A	
R5F212K2SDXXXFP (D)	8 Kbytes	1 Kbyte	PLQP0032GB-A	D version Factory programming product(1)
R5F212K4SDXXXFP (D)	16 Kbytes	1.5 Kbytes	PLQP0032GB-A	

(D): Under development

NOTE:

1. The user ROM is programmed before shipment.



NOTE:
1: Please contact Renesas Technology sales offices for the Y version.

Figure 1.1 Part Number, Memory Size, and Package of R8C/2K Group

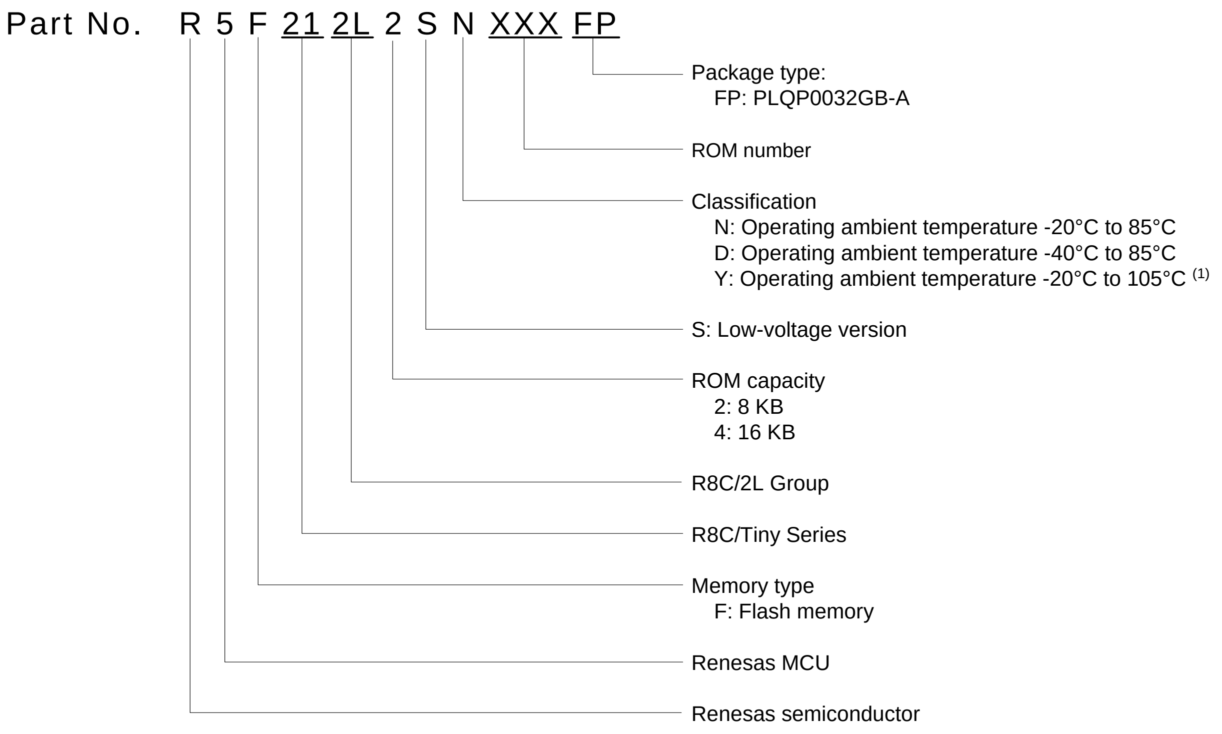
Table 1.6 Product List for R8C/2L Group **Current of Dec. 2007**

Part No.	ROM Capacity		RAM Capacity	Package Type	Remarks
	Program ROM	Data flash			
R5F212L2SNFP	8 Kbytes	1 Kbyte × 2	1 Kbyte	PLQP0032GB-A	N version
R5F212L4SNFP	16 Kbytes	1 Kbyte × 2	1.5 Kbytes	PLQP0032GB-A	
R5F212L2SDFP	8 Kbytes	1 Kbyte × 2	1 Kbyte	PLQP0032GB-A	D version
R5F212L4SDFP	16 Kbytes	1 Kbyte × 2	1.5 Kbytes	PLQP0032GB-A	
R5F212L2SNXXXFP (D)	8 Kbytes	1 Kbyte × 2	1 Kbyte	PLQP0032GB-A	N version Factory programming product(1)
R5F212L4SNXXXFP (D)	16 Kbytes	1 Kbyte × 2	1.5 Kbytes	PLQP0032GB-A	
R5F212L2SDXXXFP (D)	8 Kbytes	1 Kbyte × 2	1 Kbyte	PLQP0032GB-A	D version Factory programming product(1)
R5F212L4SDXXXFP (D)	16 Kbytes	1 Kbyte × 2	1.5 Kbytes	PLQP0032GB-A	

(D): Under development

NOTE:

1. The user ROM is programmed before shipment.



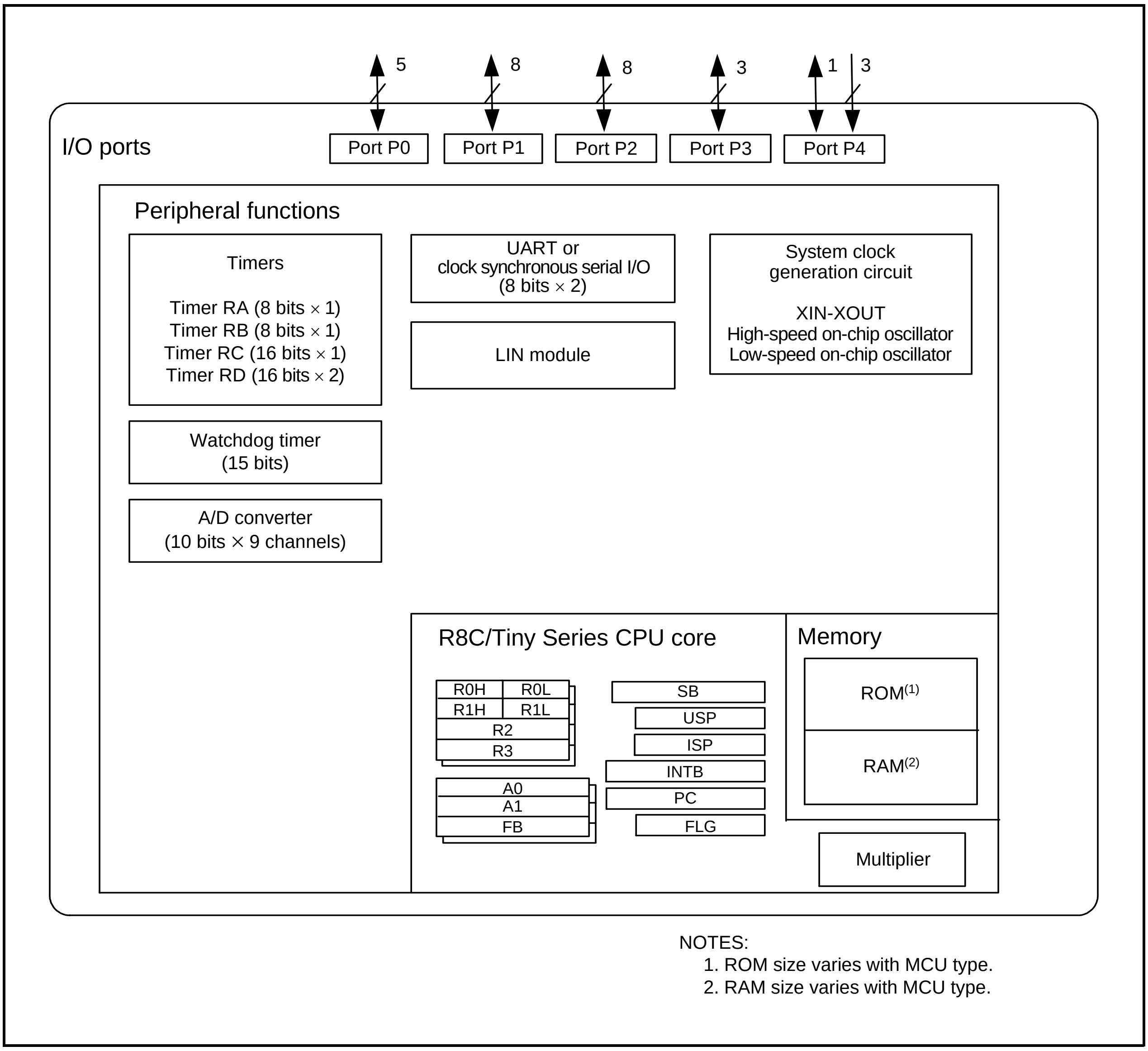
NOTE:

1: Please contact Renesas Technology sales offices for the Y version.

Figure 1.2 Part Number, Memory Size, and Package of R8C/2L Group

1.3 Block Diagram

Figure 1.3 shows a Block Diagram.

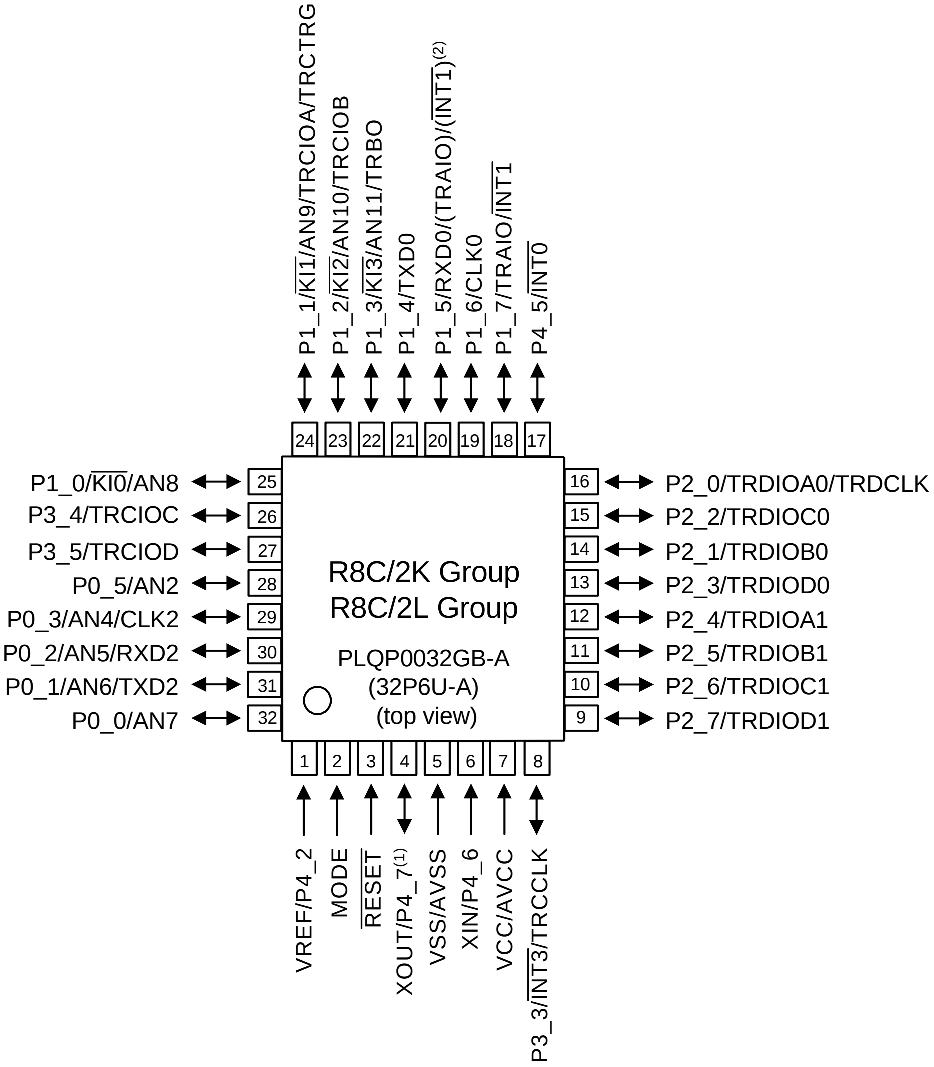


NOTES:
1. ROM size varies with MCU type.
2. RAM size varies with MCU type.

Figure 1.3 Block Diagram

1.4 Pin Assignment

Figure 1.4 shows the Pin Assignment (Top View). Table 1.7 outlines the Pin Name Information by Pin Number.



NOTES:
1. P4_7 are an input-only port.
2. Can be assigned to the pin in parentheses by a program.
3. Confirm the pin 1 position on the package by referring to the package dimensions.

Figure 1.4 Pin Assignment (Top View)

1.5 Pin Functions

Table 1.8 lists Pin Functions.

Table 1.8 Pin Functions

Item	Pin Name	I/O Type	Description
Power supply input	VCC, VSS	–	Apply 2.2 V to 5.5 V to the VCC pin. Apply 0 V to the VSS pin.
Analog power supply input	AVCC, AVSS	–	Power supply for the A/D converter. Connect a capacitor between AVCC and AVSS.
Reset input	$\overline{\text{RESET}}$	I	Input “L” on this pin resets the MCU.
MODE	MODE	I	Connect this pin to VCC via a resistor.
XIN clock input	XIN	I	These pins are provided for XIN clock generation circuit I/O. Connect a ceramic resonator or a crystal oscillator between the XIN and XOUT pins(1). To use an external clock, input it to the XIN pin and leave the XOUT pin open.
XIN clock output	XOUT	O	
$\overline{\text{INT}}$ interrupt input	$\overline{\text{INT0}}$, $\overline{\text{INT1}}$, $\overline{\text{INT3}}$	I	$\overline{\text{INT}}$ interrupt input pins. $\overline{\text{INT0}}$ is timer RB, timer RC and timer RD input pins.
Key input interrupt	$\overline{\text{KI0}}$ to $\overline{\text{KI3}}$	I	Key input interrupt input pins
Timer RA	TRAIO	I/O	Timer RA I/O pin
Timer RB	TRBO	O	Timer RB output pin
Timer RC	TRCCLK	I	External clock input pin
	TRCTRG	I	External trigger input pin
	TRCIOA, TRCIOB, TRCIOC, TRCIOD	I/O	Timer RC I/O pins
Timer RD	TRDIOA0, TRDIOA1, TRDIOB0, TRDIOB1, TRDIOC0, TRDIOC1, TRDIOD0, TRDIOD1	I/O	Timer RD I/O pins
	TRDCLK	I	External clock input pin
Serial interface	CLK0, CLK2	I/O	Transfer clock I/O pins
	RXD0, RXD2	I	Serial data input pins
	TXD0, TXD2	O	Serial data output pins
Reference voltage input	VREF	I	Reference voltage input pin to A/D converter
A/D converter	AN2, AN4 to AN11	I	Analog input pins to A/D converter
I/O port	P0_0 to P0_3, P0_5, P1_0 to P1_7, P2_0 to P2_7, P3_3 to P3_5, P4_5,	I/O	CMOS I/O ports. Each port has an I/O select direction register, allowing each pin in the port to be directed for input or output individually. Any port set to input can be set to use a pull-up resistor or not by a program. P2_0 to P2_7 also function as LED drive ports.
Input port	P4_2, P4_6, P4_7	I	Input-only ports

I: Input O: Output I/O: Input and output

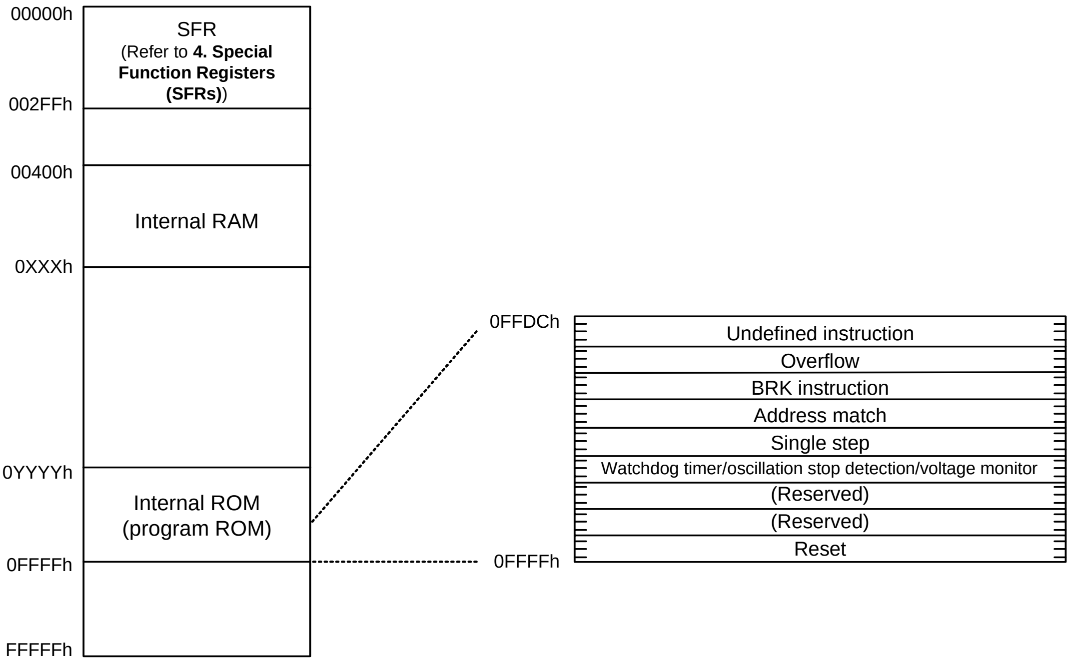
NOTE:

1. Refer to the oscillator manufacturer for oscillation characteristics.

3. Memory

3.1 R8C/2K Group

Figure 3.1 is a Memory Map of R8C/2K Group. The R8C/2K Group has 1 Mbyte of address space from addresses 00000h to FFFFFh.
The internal ROM is allocated lower addresses, beginning with address 0FFFFh. For example, a 16-Kbyte internal ROM area is allocated addresses 0C000h to 0FFFFh.
The fixed interrupt vector table is allocated addresses 0FFDCh to 0FFFFh. They store the starting address of each interrupt routine.
The internal RAM is allocated higher addresses beginning with address 00400h. For example, a 1.5-Kbyte internal RAM area is allocated addresses 00400h to 009FFh. The internal RAM is used not only for storing data but also for calling subroutines and as stacks when interrupt requests are acknowledged.
Special function registers (SFRs) are allocated addresses 00000h to 002FFh. The peripheral function control registers are allocated here. All addresses within the SFR, which have nothing allocated are reserved for future use and cannot be accessed by users.



NOTE:
1. The blank regions are reserved. Do not access locations in these regions.

Part Number	Internal ROM		Internal RAM	
	Size	Address 0YYYYh	Size	Address 0XXXXh
R5F212K2SNFP, R5F212K2SDFP, R5F212K2SNXXXFP, R5F212K2SDXXXFP	8 Kbytes	0E000h	1 Kbyte	007FFh
R5F212K4SNFP, R5F212K4SDFP, R5F212K4SNXXXFP, R5F212K4SDXXXFP	16 Kbytes	0C000h	1.5 Kbytes	009FFh

Figure 3.1 Memory Map of R8C/2K Group

Table 4.2 SFR Information (2)(1)

Address	Register	Symbol	After reset
0040h			
0041h			
0042h			
0043h			
0044h			
0045h			
0046h			
0047h	Timer RC Interrupt Control Register	TRCIC	XXXXX000b
0048h	Timer RD0 Interrupt Control Register	TRD0IC	XXXXX000b
0049h	Timer RD1 Interrupt Control Register	TRD1IC	XXXXX000b
004Ah			
004Bh	UART2 Transmit Interrupt Control Register	S2TIC	XXXXX000b
004Ch	UART2 Receive Interrupt Control Register	S2RIC	XXXXX000b
004Dh	Key Input Interrupt Control Register	KUPIC	XXXXX000b
004Eh	A/D Conversion Interrupt Control Register	ADIC	XXXXX000b
004Fh			
0050h			
0051h	UART0 Transmit Interrupt Control Register	S0TIC	XXXXX000b
0052h	UART0 Receive Interrupt Control Register	S0RIC	XXXXX000b
0053h			
0054h			
0055h			
0056h	Timer RA Interrupt Control Register	TRAIC	XXXXX000b
0057h			
0058h	Timer RB Interrupt Control Register	TRBIC	XXXXX000b
0059h	INT1 Interrupt Control Register	INT1IC	XX00X000b
005Ah	INT3 Interrupt Control Register	INT3IC	XX00X000b
005Bh			
005Ch			
005Dh	INT0 Interrupt Control Register	INT0IC	XX00X000b
005Eh			
005Fh			
0060h			
0061h			
0062h			
0063h			
0064h			
0065h			
0066h			
0067h			
0068h			
0069h			
006Ah			
006Bh			
006Ch			
006Dh			
006Eh			
006Fh			
0070h			
0071h			
0072h			
0073h			
0074h			
0075h			
0076h			
0077h			
0078h			
0079h			
007Ah			
007Bh			
007Ch			
007Dh			
007Eh			
007Fh			

X: Undefined
NOTE:
1. The blank regions are reserved. Do not access locations in these regions.

Table 4.6 SFR Information (6)(1)

Address	Register	Symbol	After reset
0140h	Timer RD Control Register 0	TRDCR0	00h
0141h	Timer RD I/O Control Register A0	TRDIORA0	10001000b
0142h	Timer RD I/O Control Register C0	TRDIORC0	10001000b
0143h	Timer RD Status Register 0	TRDSR0	11100000b
0144h	Timer RD Interrupt Enable Register 0	TRDIER0	11100000b
0145h	Timer RD PWM Mode Output Level Control Register 0	TRDPOCR0	11111000b
0146h	Timer RD Counter 0	TRD0	00h
0147h			00h
0148h	Timer RD General Register A0	TRDGRA0	FFh
0149h			FFh
014Ah	Timer RD General Register B0	TRDGRB0	FFh
014Bh			FFh
014Ch	Timer RD General Register C0	TRDGRC0	FFh
014Dh			FFh
014Eh	Timer RD General Register D0	TRDGRD0	FFh
014Fh			FFh
0150h	Timer RD Control Register 1	TRDCR1	00h
0151h	Timer RD I/O Control Register A1	TRDIORA1	10001000b
0152h	Timer RD I/O Control Register C1	TRDIORC1	10001000b
0153h	Timer RD Status Register 1	TRDSR1	11000000b
0154h	Timer RD Interrupt Enable Register 1	TRDIER1	11100000b
0155h	Timer RD PWM Mode Output Level Control Register 1	TRDPOCR1	11111000b
0156h	Timer RD Counter 1	TRD1	00h
0157h			00h
0158h	Timer RD General Register A1	TRDGRA1	FFh
0159h			FFh
015Ah	Timer RD General Register B1	TRDGRB1	FFh
015Bh			FFh
015Ch	Timer RD General Register C1	TRDGRC1	FFh
015Dh			FFh
015Eh	Timer RD General Register D1	TRDGRD1	FFh
015Fh			FFh
0160h	UART2 Transmit/Receive Mode Register	U2MR	00h
0161h	UART2 Bit Rate Register	U2BRG	XXh
0162h	UART2 Transmit Buffer Register	U2TB	XXh
0163h			XXh
0164h	UART2 Transmit/Receive Control Register 0	U2C0	00001000b
0165h	UART2 Transmit/Receive Control Register 1	U2C1	00000010b
0166h	UART2 Receive Buffer Register	U2RB	XXh
0167h			XXh
0168h			
0169h			
016Ah			
016Bh			
016Ch			
016Dh			
016Eh			
016Fh			
0170h			
0171h			
0172h			
0173h			
0174h			
0175h			
0176h			
0177h			
0178h			
0179h			
017Ah			
017Bh			
017Ch			
017Dh			
017Eh			
017Fh			

X: Undefined
NOTE:
1. The blank regions are reserved. Do not access locations in these regions.

Table 4.7 SFR Information (7)(1)

Address	Register	Symbol	After reset
0180h			
0181h			
0182h			
0183h			
0184h			
0185h			
0186h			
0187h			
0188h			
0189h			
018Ah			
018Bh			
018Ch			
018Dh			
018Eh			
018Fh			
0190h			
0191h			
0192h			
0193h			
0194h			
0195h			
0196h			
0197h			
0198h			
0199h			
019Ah			
019Bh			
019Ch			
019Dh			
019Eh			
019Fh			
01A0h			
01A1h			
01A2h			
01A3h			
01A4h			
01A5h			
01A6h			
01A7h			
01A8h			
01A9h			
01AAh			
01ABh			
01ACh			
01ADh			
01AEh			
01AFh			
01B0h			
01B1h			
01B2h			
01B3h	Flash Memory Control Register 4	FMR4	01000000b
01B4h			
01B5h	Flash Memory Control Register 1	FMR1	1000000Xb
01B6h			
01B7h	Flash Memory Control Register 0	FMR0	00000001b
01B8h			
01B9h			
01BAh			
01BBh			
01BCh			
01BDh			
01BEh			
01BFh			

FFFFh	Option Function Select Register	OFS	(Note 2)

X: Undefined
NOTES:

1. The blank regions are reserved. Do not access locations in these regions.
2. The OFS register cannot be changed by a program. Use a flash programmer to write to it.

Table 5.3 A/D Converter Characteristics

Symbol	Parameter		Conditions	Standard			Unit
				Min.	Typ.	Max.	
–	Resolution		V_{ref} = AV_{CC}	–	–	10	Bits
–	Absolute accuracy	10-bit mode	ϕ_{AD} = 10 MHz, V_{ref} = AV_{CC} = 5.0 V	–	–	±3	LSB
		8-bit mode	ϕ_{AD} = 10 MHz, V_{ref} = AV_{CC} = 5.0 V	–	–	±2	LSB
		10-bit mode	ϕ_{AD} = 10 MHz, V_{ref} = AV_{CC} = 3.3 V	–	–	±5	LSB
		8-bit mode	ϕ_{AD} = 10 MHz, V_{ref} = AV_{CC} = 3.3 V	–	–	±2	LSB
R_{ladder}	Resistor ladder		V_{ref} = AV_{CC}	10	–	40	kΩ
t_{conv}	Conversion time	10-bit mode	ϕ_{AD} = 10 MHz, V_{ref} = AV_{CC} = 5.0 V	3.3	–	–	µs
		8-bit mode	ϕ_{AD} = 10 MHz, V_{ref} = AV_{CC} = 5.0 V	2.8	–	–	µs
V_{ref}	Reference voltage			2.2	–	AV_{CC}	V
V_{IA}	Analog input voltage(2)			0	–	AV_{CC}	V
–	A/D operating clock frequency	Without sample and hold	V_{ref} = AV_{CC} = 2.7 to 5.5 V	0.25	–	10	MHz
		With sample and hold	V_{ref} = AV_{CC} = 2.7 to 5.5 V	1	–	10	MHz

NOTES:

1. AV_{CC} = 2.7 to 5.5 V at T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.
2. When the analog input voltage is over the reference voltage, the A/D conversion result will be 3FFh in 10-bit mode and FFh in 8-bit mode.

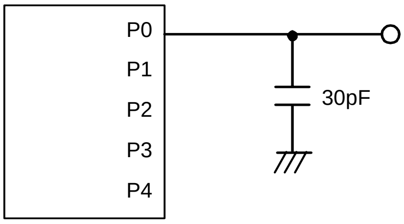


Figure 5.1 Ports P0 to P4 Timing Measurement Circuit

Table 5.4 Flash Memory (Program ROM) Electrical Characteristics

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Program/erase endurance(2)	R8C/2K Group	100(3)	–	–	times
		R8C/2L Group	1,000(3)	–	–	times
–	Byte program time		–	50	400	µs
–	Block erase time		–	0.4	9	s
$t_{d(SR-SUS)}$	Time delay from suspend request until suspend		–	–	97+CPU clock × 6 cycles	µs
–	Interval from erase start/restart until following suspend request		650	–	–	µs
–	Interval from program start/restart until following suspend request		0	–	–	ns
–	Time from suspend until program/erase restart		–	–	3+CPU clock × 4 cycles	µs
–	Program, erase voltage		2.7	–	5.5	V
–	Read voltage		2.2	–	5.5	V
–	Program, erase temperature		0	–	60	°C
–	Data hold time(7)	Ambient temperature = 55°C	20	–	–	year

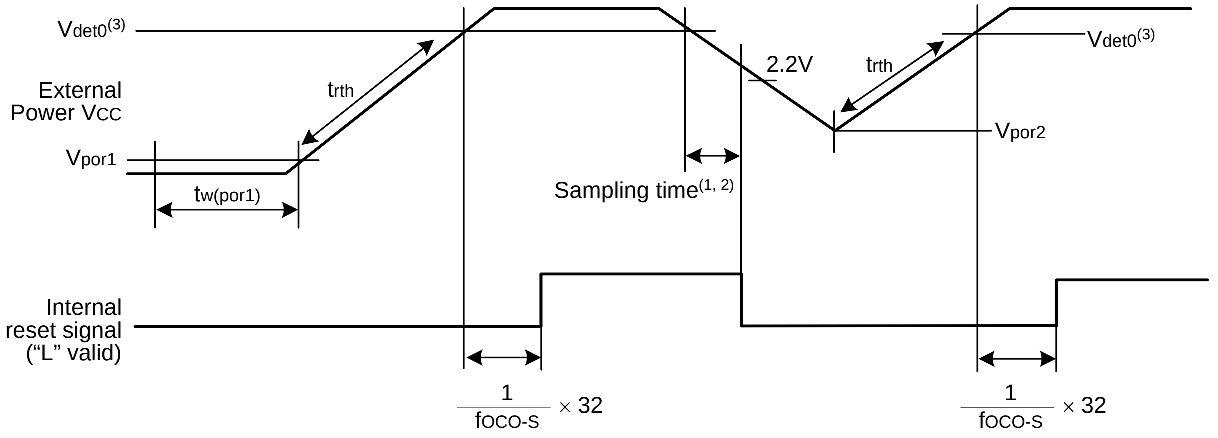
NOTES:

1. V_{CC} = 2.7 to 5.5 V at T_{opr} = 0 to 60°C, unless otherwise specified.
2. Definition of programming/erasure endurance
   The programming and erasure endurance is defined on a per-block basis.
   If the programming and erasure endurance is n (n = 100 or 10,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one.
   However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
4. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. It is also advisable to retain data on the erase count of each block and limit the number of erase operations to a certain number.
5. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
6. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
7. The data hold time includes time that the power supply is off or the clock is not supplied.

Table 5.9 Power-on Reset Circuit, Voltage Monitor 0 Reset Electrical Characteristics(3)

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{por1}	Power-on reset valid voltage(4)		–	–	0.1	V
V_{por2}	Power-on reset or voltage monitor 0 reset valid voltage		0	–	V_{det0}	V
t_{rth}	External power V_{CC} rise gradient(2)		20	–	–	mV/msec

NOTES:
1. The measurement condition is T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.
2. This condition (external power V_{CC} rise gradient) does not apply if $V_{CC} \geq 1.0$ V.
3. To use the power-on reset function, enable voltage monitor 0 reset by setting the LVD0ON bit in the OFS register to 0, the VW0C0 and VW0C6 bits in the VW0C register to 1 respectively, and the VCA25 bit in the VCA2 register to 1.
4. $t_{w(por1)}$ indicates the duration the external power V_{CC} must be held below the effective voltage (V_{por1}) to enable a power on reset. When turning on the power for the first time, maintain $t_{w(por1)}$ for 30 s or more if $-20°C \leq T_{opr} \leq 85°C$, maintain $t_{w(por1)}$ for 3,000 s or more if $-40°C \leq T_{opr} < -20°C$.



NOTES:
1. When using the voltage monitor 0 digital filter, ensure that the voltage is within the MCU operation voltage range (2.2 V or above) during the sampling time.
2. The sampling clock can be selected. Refer to **6. Voltage Detection Circuit** for details.
3. V_{det0} indicates the voltage detection level of the voltage detection 0 circuit. Refer to **6. Voltage Detection Circuit** for details.

Figure 5.3 Reset Circuit Electrical Characteristics

Table 5.10 High-speed On-Chip Oscillator Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
fOCO40M	High-speed on-chip oscillator frequency temperature • supply voltage dependence	V_{CC} = 2.7 V to 5.5 V $-20°C \le T_{opr} \le 85°C$(2)	39.2	40	40.8	MHz
		V_{CC} = 2.7 V to 5.5 V $-40°C \le T_{opr} \le 85°C$(2)	39.0	40	41.0	MHz
		V_{CC} = 2.2 V to 5.5 V $-20°C \le T_{opr} \le 85°C$(3)	35.2	40	44.8	MHz
		V_{CC} = 2.2 V to 5.5 V $-40°C \le T_{opr} \le 85°C$(3)	34.0	40	46.0	MHz
	High-speed on-chip oscillator frequency when correction value in FRA7 register is written to FRA1 register(4)	V_{CC} = 5.0 V, T_{opr} = 25°C	–	36.864	–	MHz
		V_{CC} = 2.7 V to 5.5 V $-20°C \le T_{opr} \le 85°C$	–3%	–	3%	%
–	Value in FRA1 register after reset		08h	–	F7h	–
–	Oscillation frequency adjustment unit of high-speed on-chip oscillator	Adjust FRA1 register (value after reset) to -1	–	+0.3	–	MHz
–	Oscillation stability time	V_{CC} = 5.0 V, T_{opr} = 25°C	–	10	100	µs
–	Self power consumption at oscillation	V_{CC} = 5.0 V, T_{opr} = 25°C	–	550	–	µA

NOTES:
1. V_{CC} = 2.2 to 5.5 V, T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.
2. These standard values show when the FRA1 register value after reset is assumed.
3. These standard values show when the corrected value of the FRA6 register is written to the FRA1 register.
4. This enables the setting errors of bit rates such as 9600 bps and 38400 bps to be 0% when the serial interface is used in UART mode.

Table 5.11 Low-speed On-Chip Oscillator Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
fOCO-S	Low-speed on-chip oscillator frequency		30	125	250	kHz
–	Oscillation stability time		–	10	100	µs
–	Self power consumption at oscillation	V_{CC} = 5.0 V, T_{opr} = 25°C	–	15	–	µA

NOTE:
1. V_{CC} = 2.2 to 5.5 V, T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.

Table 5.12 Power Supply Circuit Timing Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
$t_{d(P-R)}$	Time for internal power supply stabilization during power-on(2)		1	–	2000	µs
$t_{d(R-S)}$	STOP exit time(3)		–	–	150	µs

NOTES:
1. The measurement condition is V_{CC} = 2.2 to 5.5 V and T_{opr} = 25°C.
2. Waiting time until the internal power supply generation circuit stabilizes during power-on.
3. Time until system clock supply starts after the interrupt is acknowledged to exit stop mode.

Table 5.13 Electrical Characteristics (1) [V_{CC} = 5 V]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V_{OH}	Output “H” voltage	Except P2_0 to P2_7, XOUT	$I_{OH} = -5$ mA		$V_{CC} - 2.0$	–	V_{CC}	V
			$I_{OH} = -200$ µA		$V_{CC} - 0.5$	–	V_{CC}	V
		P2_0 to P2_7	Drive capacity HIGH	$I_{OH} = -20$ mA	$V_{CC} - 2.0$	–	V_{CC}	V
			Drive capacity LOW	$I_{OH} = -5$ mA	$V_{CC} - 2.0$	–	V_{CC}	V
		XOUT	Drive capacity HIGH	$I_{OH} = -1$ mA	$V_{CC} - 2.0$	–	V_{CC}	V
			Drive capacity LOW	$I_{OH} = -500$ µA	$V_{CC} - 2.0$	–	V_{CC}	V
V_{OL}	Output “L” voltage	Except P2_0 to P2_7, XOUT	$I_{OL} = 5$ mA		–	–	2.0	V
			$I_{OL} = 200$ µA		–	–	0.45	V
		P2_0 to P2_7	Drive capacity HIGH	$I_{OL} = 20$ mA	–	–	2.0	V
			Drive capacity LOW	$I_{OL} = 5$ mA	–	–	2.0	V
		XOUT	Drive capacity HIGH	$I_{OL} = 1$ mA	–	–	2.0	V
			Drive capacity LOW	$I_{OL} = 500$ µA	–	–	2.0	V
V_{T+}-V_{T-}	Hysteresis	$\overline{\text{INT0}}$, $\overline{\text{INT1}}$, $\overline{\text{INT3}}$, $\overline{\text{KI0}}$, $\overline{\text{KI1}}$, $\overline{\text{KI2}}$, $\overline{\text{KI3}}$, TRAIO, RXD0, RXD2, CLK0, CLK2			0.1	0.5	–	V
		$\overline{\text{RESET}}$			0.1	1.0	–	V
I_{IH}	Input “H” current		VI = 5 V, V_{CC} = 5 V		–	–	5.0	µA
I_{IL}	Input “L” current		VI = 0 V, V_{CC} = 5 V		–	–	–5.0	µA
R_{PULLUP}	Pull-up resistance		VI = 0 V, V_{CC} = 5 V		30	50	167	kΩ
R_{fXIN}	Feedback resistance	XIN			–	1.0	–	MΩ
V_{RAM}	RAM hold voltage		During stop mode		1.8	–	–	V

NOTE:

1. V_{CC} = 4.2 to 5.5 V at T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), f(XIN) = 20 MHz, unless otherwise specified.

Table 5.14 Electrical Characteristics (2) [Vcc = 5 V]
(Topr = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter	Condition		Standard			Unit
				Min.	Typ.	Max.	
ICC	Power supply current (VCC = 3.3 to 5.5 V) Single-chip mode, output pins are open, other pins are VSS	High-speed clock mode	XIN = 20 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	10	17	mA
			XIN = 16 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	9	15	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	6	–	mA
			XIN = 20 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	5	–	mA
			XIN = 16 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	4	–	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	2.5	–	mA
		High-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator on fOCO = 20 MHz Low-speed on-chip oscillator on = 125 kHz No division	–	10	15	mA
			XIN clock off High-speed on-chip oscillator on fOCO = 20 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	4	–	mA
			XIN clock off High-speed on-chip oscillator on fOCO = 10 MHz Low-speed on-chip oscillator on = 125 kHz No division	–	5.5	10	mA
			XIN clock off High-speed on-chip oscillator on fOCO = 10 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	2.5	–	mA
		Low-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8, FMR47 = 1	–	130	300	µA

Table 5.20 Electrical Characteristics (1) [V_{CC} = 3 V]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V_{OH}	Output “H” voltage	Except P2_0 to P2_7, XOUT	I_{OH} = –1 mA		V_{CC} – 0.5	–	V_{CC}	V
		P2_0 to P2_7	Drive capacity HIGH	I_{OH} = –5 mA	V_{CC} – 0.5	–	V_{CC}	V
			Drive capacity LOW	I_{OH} = –1 mA	V_{CC} – 0.5	–	V_{CC}	V
		XOUT	Drive capacity HIGH	I_{OH} = –0.1 mA	V_{CC} – 0.5	–	V_{CC}	V
			Drive capacity LOW	I_{OH} = –50 μA	V_{CC} – 0.5	–	V_{CC}	V
V_{OL}	Output “L” voltage	Except P2_0 to P2_7, XOUT	I_{OL} = 1 mA		–	–	0.5	V
		P2_0 to P2_7	Drive capacity HIGH	I_{OL} = 5 mA	–	–	0.5	V
			Drive capacity LOW	I_{OL} = 1 mA	–	–	0.5	V
		XOUT	Drive capacity HIGH	I_{OL} = 0.1 mA	–	–	0.5	V
			Drive capacity LOW	I_{OL} = 50 μA	–	–	0.5	V
V_{T+}-V_{T-}	Hysteresis	$\overline{INT0}$, $\overline{INT1}$, $\overline{INT3}$, KI0, KI1, KI2, KI3, TRAIO, RXD0, RXD2, CLK0, CLK2			0.1	0.3	–	V
		$\overline{RESET}$			0.1	0.4	–	V
I_{IH}	Input “H” current		VI = 3 V, V_{CC} = 3 V		–	–	4.0	μA
I_{IL}	Input “L” current		VI = 0 V, V_{CC} = 3 V		–	–	–4.0	μA
R_{PULLUP}	Pull-up resistance		VI = 0 V, V_{CC} = 3 V		66	160	500	kΩ
R_{fXIN}	Feedback resistance	XIN			–	3.0	–	MΩ
V_{RAM}	RAM hold voltage		During stop mode		1.8	–	–	V

NOTE:

1. V_{CC} =2.7 to 3.3 V at T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), f(XIN) = 10 MHz, unless otherwise specified.

Table 5.21 Electrical Characteristics (2) [Vcc = 3 V]
(T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter	Condition		Standard			Unit
				Min.	Typ.	Max.	
I_{CC}	Power supply current (V_{CC} = 2.7 to 3.3 V) Single-chip mode, output pins are open, other pins are V_{SS}	High-speed clock mode	XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	6	–	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	2	–	mA
		High-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator on fOCO = 10 MHz Low-speed on-chip oscillator on = 125 kHz No division	–	5	9	mA
			XIN clock off High-speed on-chip oscillator on fOCO = 10 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	2	–	mA
		Low-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8, FMR47 = 1	–	130	300	μA
		Wait mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	25	70	μA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	23	55	μA
		Stop mode	XIN clock off, T_{opr} = 25°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	0.7	3.0	μA
			XIN clock off, T_{opr} = 85°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	1.1	–	μA

Table 5.27 Electrical Characteristics (2) [Vcc = 2.2 V] (Topr = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter	Condition		Standard			Unit
				Min.	Typ.	Max.	
ICC	Power supply current (VCC = 2.2 to 2.7 V) Single-chip mode, output pins are open, other pins are VSS	High-speed clock mode	XIN = 5 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	3.5	–	mA
			XIN = 5 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	1.5	–	mA
		High-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator on fOCO = 5 MHz Low-speed on-chip oscillator on = 125 kHz No division	–	3.5	–	mA
			XIN clock off High-speed on-chip oscillator on fOCO = 5 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	1.5	–	mA
		Low-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8, FMR47 = 1	–	100	230	µA
		Wait mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	22	60	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	20	55	µA
		Stop mode	XIN clock off, Topr = 25°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	0.7	3.0	µA
			XIN clock off, Topr = 85°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	1.1	–	µA

Timing requirements
(Unless Otherwise Specified: V_{CC} = 2.2 V, V_{SS} = 0 V at T_{opr} = 25°C) [V_{CC} = 2.2 V]

Table 5.28 XIN Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(XIN)}$	XIN input cycle time	200	–	ns
$t_{WH(XIN)}$	XIN input “H” width	90	–	ns
$t_{WL(XIN)}$	XIN input “L” width	90	–	ns

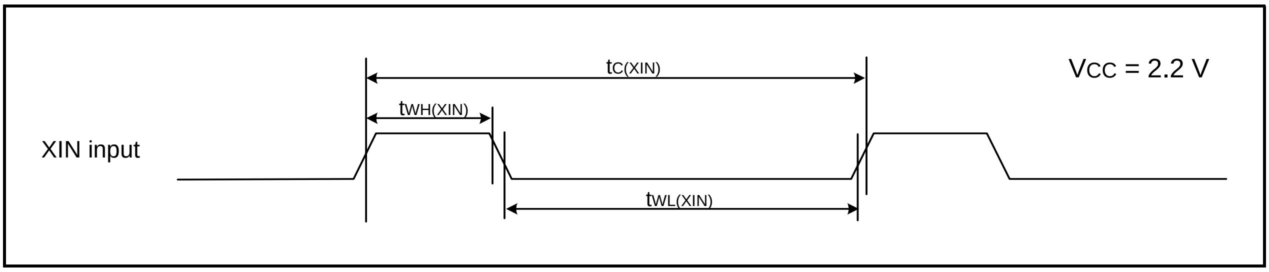


Figure 5.12 XIN Input Timing Diagram when V_{CC} = 2.2 V

Table 5.29 TRAIO Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TRAIO)}$	TRAIO input cycle time	500	–	ns
$t_{WH(TRAIO)}$	TRAIO input “H” width	200	–	ns
$t_{WL(TRAIO)}$	TRAIO input “L” width	200	–	ns

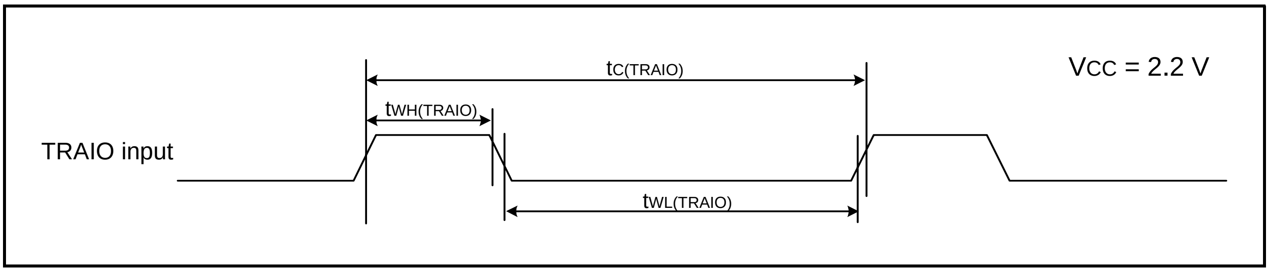


Figure 5.13 TRAIO Input Timing Diagram when V_{CC} = 2.2 V

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